ASSP

BIPOLAR

SWITCHING REGULATOR CONTROLLER

MB3769A

■ DESCRIPTION

The Fujitsu MB3769A is a pulse-width-modulation controller which is applied to fixed frequency pulse modulation technique. The MB3769A contains wide band width Op-Amp and high speed comparator to construct very high speed switching regulator system up to 700 kHz. Output is suitable for power MOS FET drive owing to adoption of totem pole output.

The MB3769A provides stand-by mode at low voltage power supply when it is applied in primary control system.

■ FEATURES

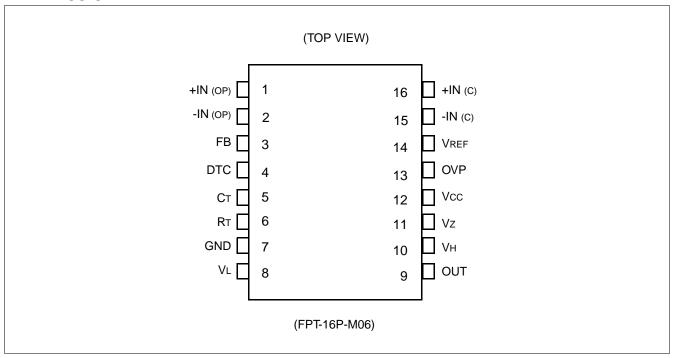
- High frequency oscillator (f = 1 kHz to 700 kHz)
- On-chip wide band frequency operation amplifier (BW = 8 MHz Typ)
- On-chip high speed comparator (td = 120 ns Typ)
- Internal reference voltage generator provides a stable reference supply (5 V ± 2%)
- Low power dissipation (1.5 mA Typ at standby mode, 8 mA Typ at operating mode)
- Output current ± 100 mA (± 600 mA at peak)
- High speed switching operation (tr = 60 ns, tf = 30 ns, CL = 1000 pF Typ)
- · Adjustable Dead-time
- On-chip soft start and quick shut down functions
- Internal circuitry prohibits double pulse at dynamic current limit operation
- Under voltage lock out function (OFF to ON: 10 V Typ, ON to OFF: 8 V Typ)
- On-chip output shut down circuit with latch function at over voltage
- On-chip Zener diode (15 V)
- One type of package (SOP-16pin : 1 type)

■ APPLICATIONS

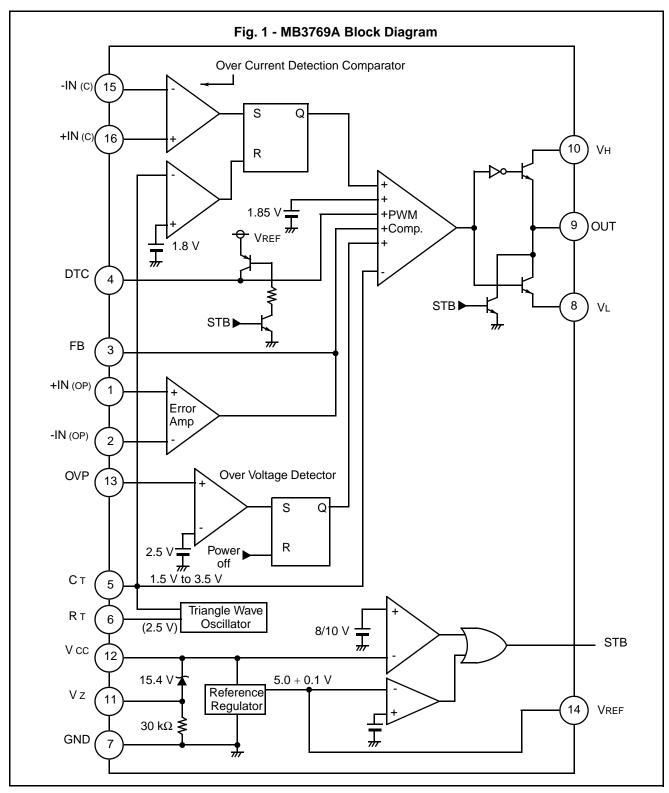
- Power supply module
- Industrial Equipment
- AC/DC Converter etc.



■ PIN ASSIGNMENT



■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	R	l lni4		
Parameter	Symbol	Min	Max	Unit	
Power Supply Voltage	Vcc	_	20	V	
Output Current	lout	_	120 (660*1)	mA	
Operation Amp Input Voltage	Vin (OP)	_	Vcc + 0.3 (≤ 20)	V	
Power Dissipation : SOP	PD	_	620*2	mW	
Storage Temperature	Tstg	-55	+125	°C	

^{*1 :} Duty ≤ 5%

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

^{*2 :} Ta = +25 °C, SOP package is mounted on the epoxy board. (4 cm x 4 cm x 0.15 cm)

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Cymbol		l Init		
Faranietei	Symbol	Min	Тур	Max	Unit
Power Supply Voltage	Vcc	12	15	18	V
Output Current (DC)	Іоит	-100	-	+100	mA
Output Current (Peak)	OUT PEAK	-600	-	+600	mA
Operation Amp Input voltage	VINOP	-0.2	0 to VREF	VCC-3	V
FB Sink Current	Isink	-	-	0.3	mA
FB Source Current	Isource	-	-	2	mA
Compositor Innut Valtage	VINC+	-0.3	0 to 3	VCC	V
Comparator Input Voltage	VINC-	-0.3	0 to 2	2.5	V
Reference Section Output Current	IREF	-	2	10	mA
Timing Resistor	RT	9	18	50	kΩ
Timing Capacitor	Ст	100	680	10 ⁶	pF
Oscillator Frequency	fosc	1	100	700	kHz
Zener Current	Iz	-	-	5	mA
Operating Ambient Temperature: SOP	Та	-30	+25	+75	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(Vcc=15V, Ta=+25°C)

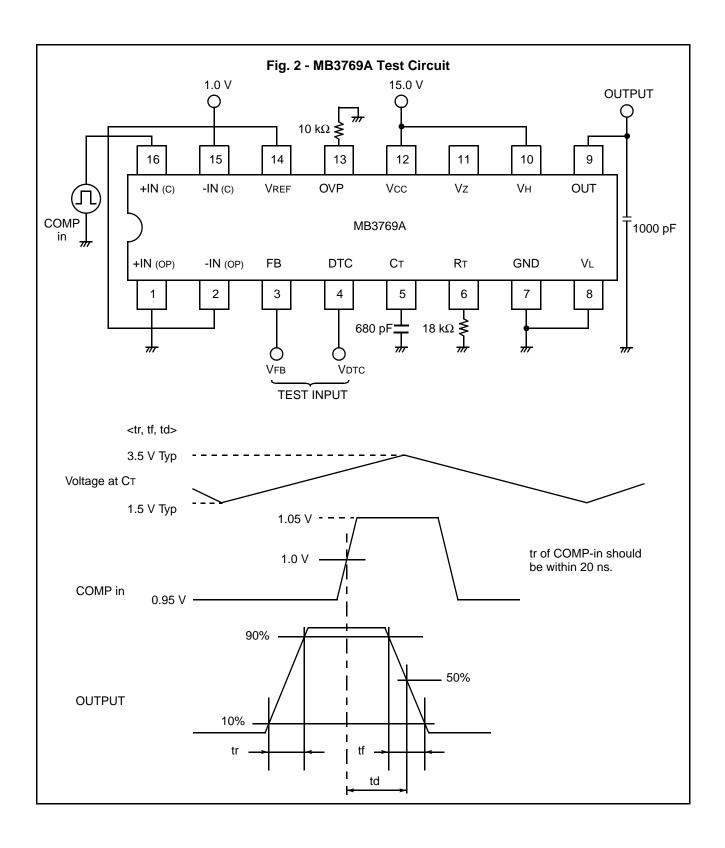
Parameter		Symbol	Condition	Value			Unit	
		Зупівої	Condition	Min	Тур	Max	Unit	
	Output Voltage		V _{REF}	Iref = 1 mA	4.9	5.0	5.1	V
	Input Regulation	Input Regulation		12 V ≤ Vcc ≤ 18 V	-	2	15	mV
Reference Section	Load Regulation	n	ΔVR ld	1 mA ≤ lref ≤10 mA	-	-1	-15	mV
	Temp. Stability		ΔVR temp	-30 °C ≤ Ta ≤ +85 °C	-	±200	±750	μV/ °C
	Short Circuit Ou	utput Current	Isc	V _{REF} = 0 V	15	40	-	mA
Oscillator	Oscillator Frequ	iency	fosc	R _T = 18 kΩ C _T = 680 pF	90	100	110	kHz
Section	Voltage Stability	′	Δf oscin	12 V ≤ Vcc ≤ 18 V	-	±0.03	-	%
	Temp. Stability		Δf osc / ΔT	-30 °C ≤ Ta ≤ +85 °C	-	±2	-	%
	Input Bias Current		lσ	-	-	2	10	μΑ
	Max. Duty Cycle		Dmax	Vd = 1.5 V	75	80	85	%
	Duty Cycle Set		Dset	Vd = 0.5 Vref	45	50	55	%
Dead -time Control Section	Input Threshold Voltage	0% Duty Cycle	V _{DO}	-	-	3.5	3.8	V
Coolon		Max. Duty Cycle	V _{DM}	-	1.55	1.85	-	V
	Discharge Voltage		V _{DH}	Vcc = 7 V, IDTC = -0.3 mA	4.5	-	-	V
	Input Offset Vol	tage	VIO (OP)	V ₃ = 2.5 V	-	±2	±10	mV
	Input Offset Current		IO (OP)	V ₃ = 2.5 V	-	±30	±300	nA
	Input Bias Current		IR (OP)	V ₃ = 2.5 V	-1	-0.3	-	μΑ
Error Amplifier Section	Common-Mode Input Voltage		Vcm (OP)	12 V ≤ Vcc ≤ 18 V	-0.2	-	Vcc -3	V
	Voltage Gain		AV (OP)	$0.5~V \leq V_3 \leq 4~V$	70	90	-	dB
	Band Width		BW	Av = 0 dB	-	8	-	MHz
	Slew Rate		SR	$R_L = 10 \text{ k}\Omega$, $Av = 0 \text{ dB}$	-	6	-	V/μs
	Common-Mode Rejection Rate		CMR	V _{IN} = 0 V to 10 V	65	80	-	dB
	"H" Level Outpu	t Voltage	Vон	I ₃ = -2 mA	4.0	4.6	-	V
	"L" Level Outpu	t Voltage	Vol	I ₃ = 0.3 mA	-	0.1	0.5	V

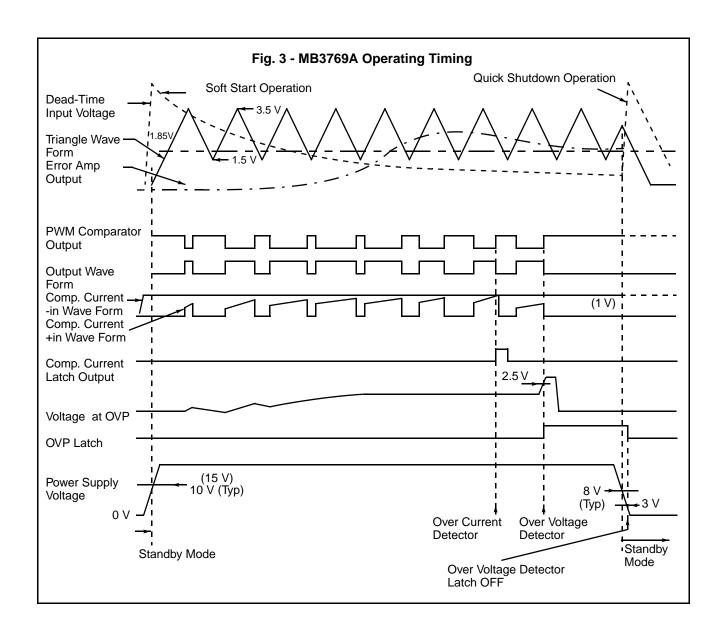
(Continued)

(Vcc=15V, Ta=+25°C)

Parameter		Symbol Condition	Value			l lmi4	
			Condition	Min	Тур	Max	Unit
	Input Offset Voltage	VIO (C)	Vin = 1 V	-	±5	±15	mV
	Input Bias Current	IIB (C)	VIN = 1 V	-5	-1	-	μΑ
Current Comparator	Common-Mode Input Voltage	Vcm (c)	-	0	-	2.5	V
	Voltage Gain	Av (c)	-	-	200	-	V/V
	Response Time	td	50 mV over drive	-	120	250	ns
PWM	0% Duty Cycle	Vopo	Rτ = 18 kΩ	-	3.5	3.8	V
Comparator Section	Max Duty Cycle	Vорм	Ст = 680 pF	1.55	1.85	-	V
	"H" Level Output Voltage	Vн	Iоит = -100 mA	12.5	13.5	-	V
	"L" Level Output Voltage	VL	Iout = 100 mA	-	1.1	1.3	V
Output Section	Rise Time	tr	CL = 1000 pF, RL = ∞	-	60	120	ns
	Fall Time	tf	CL = 1000 pF, RL = ∞	-	30	80	ns
Over	Threshold Voltage	Vovp	-	2.4	2.5	2.6	V
Voltage Detector	Input Current	liovp	VIN = 0 V	-1.0	-0.2	-	μΑ
	Vcc Reset	Vcc rst	-	2.0	3.0	4.5	V
Under	Off to On	Vтнн	-	9.2	10.0	10.8	V
Voltage Out Stop	On to Off	VTHL	-	7.2	8.0	8.8	V
Supply	Standby *	Іѕтв	R _T = 18 kΩ 4 pin Open	-	1.5	2.0	mA
	Operating	Icc	R _T = 18 kΩ	-	8.0	12.0	mA
Current	Zener Voltage	Vz	Iz = 1 mA	-	15.4	-	V
	Zener Current	lz	V11-7 = 1 V	-	0.03	-	mA

^{* :} Vcc = 8V



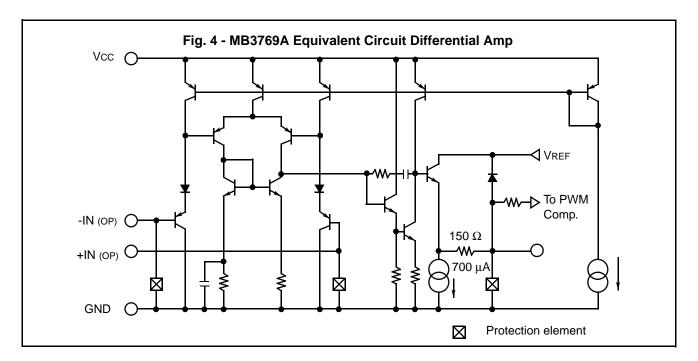


■ FUNCTIONS

1. Error Amplifier

The error amplifier detects the output voltage of the switching regulator.

The error amplifier uses a high-speed operational amplifier with an 8 MHz bandwidth (typical) and 6 V/µs slew rate (typical). For ease of use, the common mode input voltage ranges from -0.2 V to Vcc-3 V. Figure 4 shows the equivalent circuit.



2. Overcurrent Detection Comparator

There are two methods for protection of the output transistor of this device from overcurrents; one restricts the transistor's ontime if an overcurrent that flows through the output transistor is detected from an average output current, and the other detects an overcurrent in the external transistor (FET) and shuts the output down instantaneously. Using average output currents, the peak current of the external transistor (FET) cannot be detected, so an output transistor with a large safe operation area (SOA) margin is required.

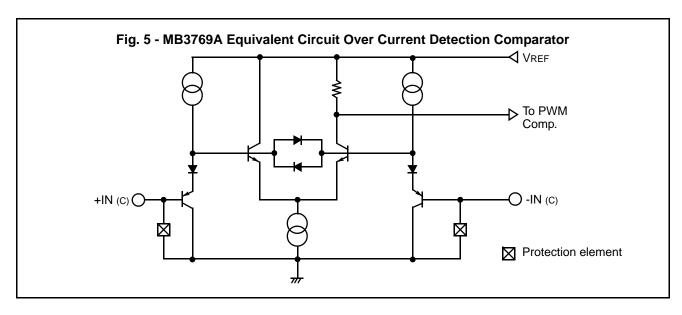
For the method of detecting overcurrents in the external transistor (FET), the output transistor can be protected against a shorted filter capacitor or power-on surge current.

The MB3769A uses dynamic current limiting to detect overcurrents in the output transistor (FET). A high-speed comparator and flip-flop are built-in.

To detect overcurrents, compare the voltage at +IN(c) of current detection resistor connected the source of the output transistor (FET), with the reference voltage (connected to -IN(c)) using a comparator. To prevent output oscillation during overcurrent, flip-flop circuit protects against double pulses occurring within a cycle.

The output of overcurrent detector is ORed with other signals at the PWM comparator. See the example "Application Example" for details on use.

Figure 5 shows the equivalent circuit of the over-current detection comparator.



3. DTC: Dead Time Control (Soft-Start and Quick Shutdown)

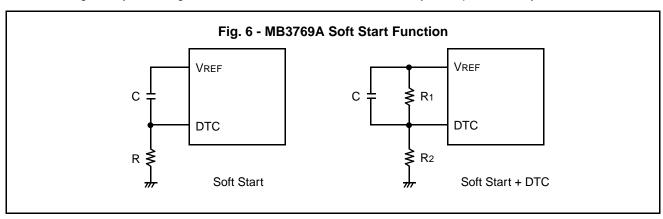
The dead time control terminal and the error amplifier output are connected to the PWM comparator.

The maximum duty cycle for VDTC (voltage applied to pin 4) is obtained from the following formula (approximate value at low frequency):

Duty Cycle =
$$(3.5 - VDTC) \times 50 (\%) [0\% \le duty cycle \le DMAX (80\%)]$$

The dead time control terminal is used to provide soft start.

In Figure 6, the DTC terminal is connected to the VREF terminal through R and C. Because capacitor C does not charge instantaneously when the power is turned on, the output transistor is kept turned off. The DTC input voltage and the output pulse width increase gradually according to the RC time constant so that the control system operates safely.



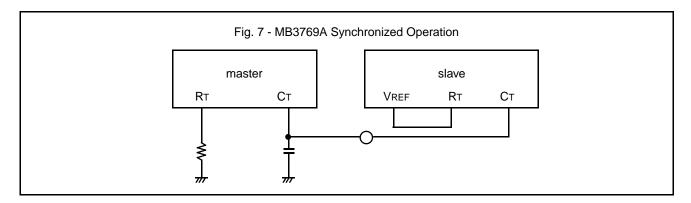
The quick shutdown function prevents soft start malfunction when the power is turned off and on quickly. After the power is shut down, soft start is disabled because the DTC terminal has low electric potential from the beginning if the power is turned on again before the capacitor is discharged. The MB3769A prevents this by turning on the discharge transistor to quickly discharge the capacitor in the stand-by mode.

4. Triangular Wave Oscillator

The oscillation frequency is expressed by the following formula:

$$fosc \simeq \begin{array}{c} 1 \\ \hline 0.8 \text{ x CT x RT} + 0.0002 \text{ ms} \end{array} \begin{bmatrix} \text{kHz} \end{bmatrix} \begin{array}{c} \text{CT} & : \mu \text{F} \\ \text{RT} & : \text{k}\Omega \end{array}$$

For master/slave synchronized operation of several MB3769As, the CT and RT terminals of the master MB3769A are connected in the usual way and the CT terminals of the master and slave device (s) are connected together. The slave MB3769A's RT terminal is connected to it's VREF terminal to disable the slave's oscillator. In this case, set $50/n \text{ k}\Omega$ (n is the number of master and slave ICs) to the upper limit of RT so that internal bias currents do not stop the master oscillation.



5. Overvoltage Detector

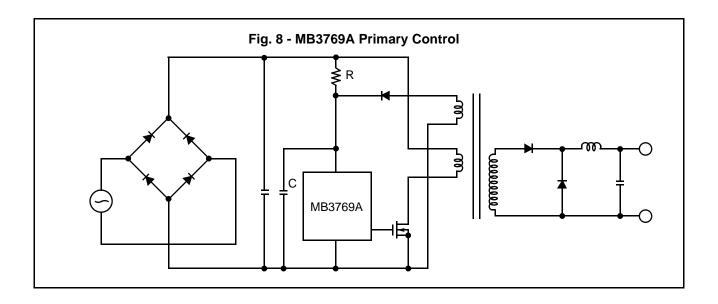
The overvoltage detection circuit shuts the system power down if the switching regulator's output voltage is abnormal or if abnormal voltage is appeared. The reference voltage is 2.5 V (VREF /2). The system power is shut down if the voltage at pin 13 rises above 2.5 V. The output is kept shut down by the latching circuit until the power supply is turned off (see Figure 3).

6. Stand-by Mode and Under-Voltage Lockout (UVLO)

Generally, VGS > 6 to 8 V is required to use power MOSFET for switching. UVLO is set so that output is on at $VCC \ge 10 \text{ V}$ (standard) when the power is turned on and is off at $VCC \le 8 \text{ V}$ (standard) when the power is turned off.

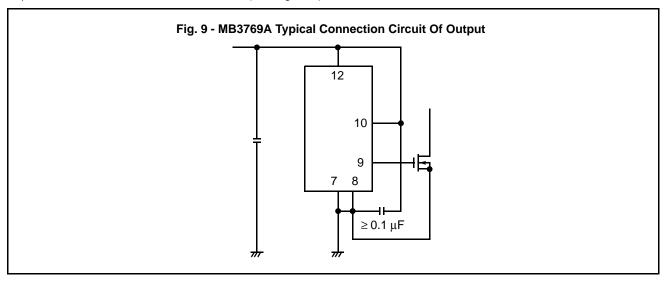
In the stand-by mode, the power supply current is limited to 2 mA or less when the output is inhibited by the UVLO circuit. When the MB3769A is operated from the 100 VAC line, the power supply current is supplied through resistor R (Figure 8). That is, the IC power supply current is supplied by the AC line through resistor R until operation starts. Current is then supplied from the transformer tertiary winding, eliminating the need for a second power supply.

Two volts (typical) of hysteresis are provided for return from operation mode to stand-by mode not to return to stand-by mode until output power is turned on or to avoid malfunction due to noise.

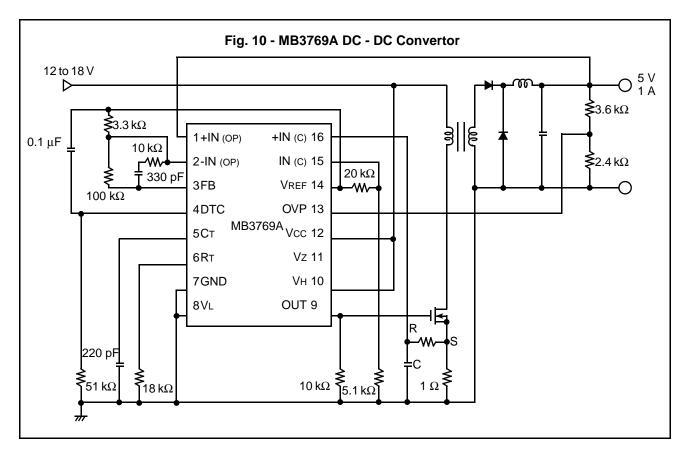


7. Output Section

Because the OUT terminal (pin 9) carries a large current, the collector and emitter of the output transistor are brought out to the VH and VL terminals. In principle, VH is connected to VCC and VL is connected to GND, but VH can be supplied from another power supply (4 V to 18 V). Note that VL and GND should be connected as close to the IC package as possible. A capacitor of $0.1 \, \mu F$ or more is inserted between VH and VL (see Figure 9).

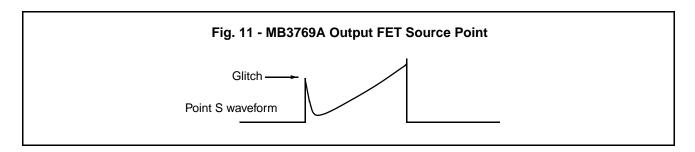


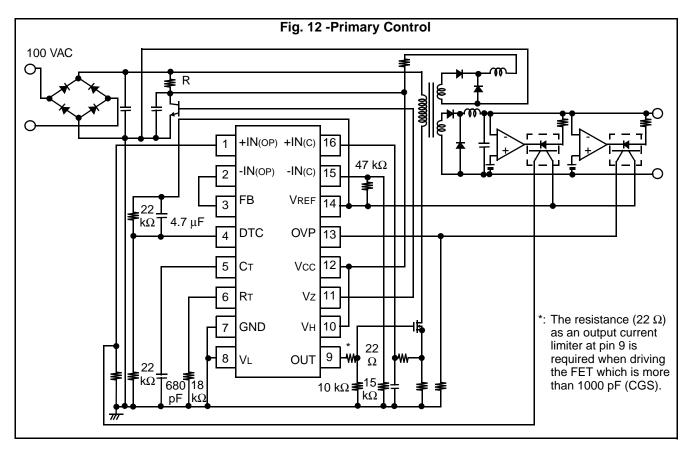
■ APPLICATION EXAMPLE

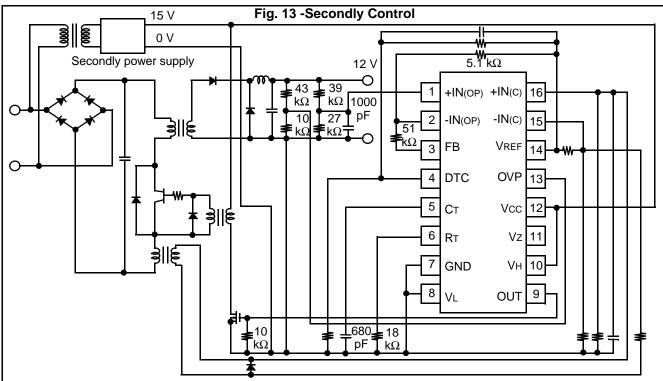


Overcurrent Protection Circuit

The waveform at the output FET source terminal is shown in Figure 11. The RC time constant must be chosen so that the voltage glitch in the waveform does not cause erroneous overcurrent detection. This time constant is should be from 5 ns to 100 ns. A detection current value depends on R or C because a waveform is weakened. To keep this glitch as small as possible, the rectifiers on the transformer secondary winding must be the fast-recovery type.

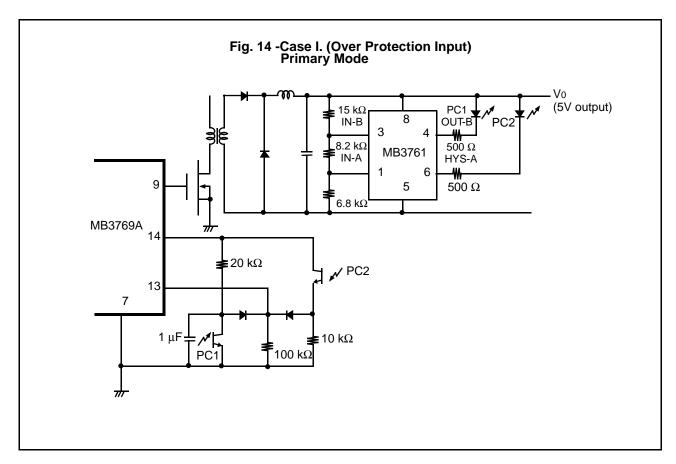


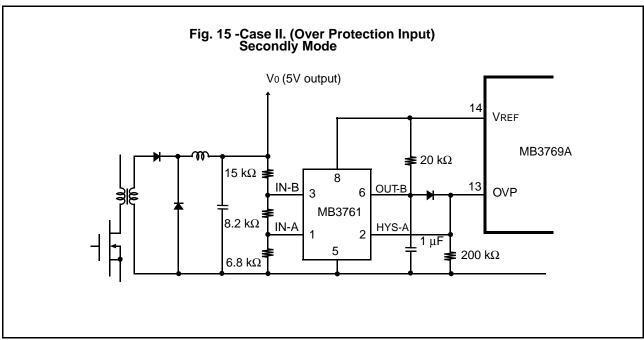




■ SHORT PROTECTION CIRCUIT

The system power can be shut down to protect the output against intermittent short-circuits or continuous overloads. This protection circuit can be configured using the OVP input as shown in Figure 14.

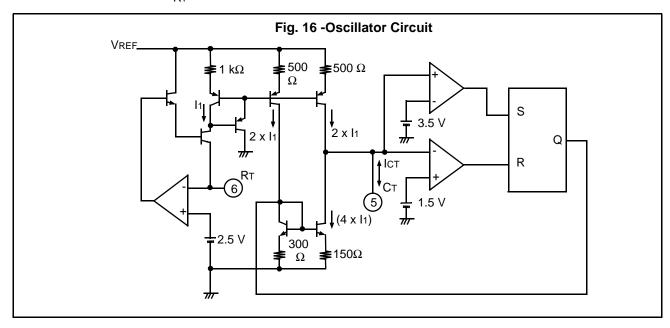




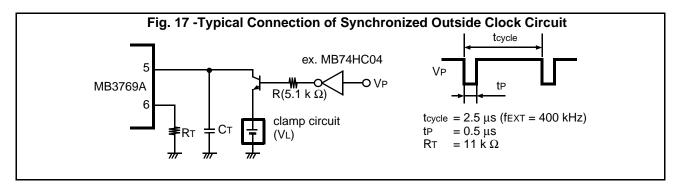
■ HOW TO SYNCHRONIZE WITH OUTSIDE CLOCK

The MB3769A oscillator circuit is shown in Figure 16. CT charge and discharge currents are expressed by the following formula:

$$ICT = \pm 2 \times I_1 = \pm \frac{5 \text{ V}}{RT}$$



This circuit shows that if the voltage at the CT terminal is set to 1.5 V or less, one oscillation cycle ends and the next cycle starts. An example of an external synchronous clock circuit is shown in Figure 17.



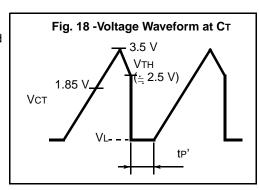
The Figure 18 shows the CT terminal waveform.

VTH may be near 2.5 V. In this case, the maximum duty cycle is restricted as shown in the formula below if tP'=0.

$$D_{\text{max}} = \frac{(3.5 - 1.85) + (3.5 - VTH)}{(3.5 - VL) + (3.5 - VTH)} \le 59\%$$
 (VL = 0 V: No clamp circuit)

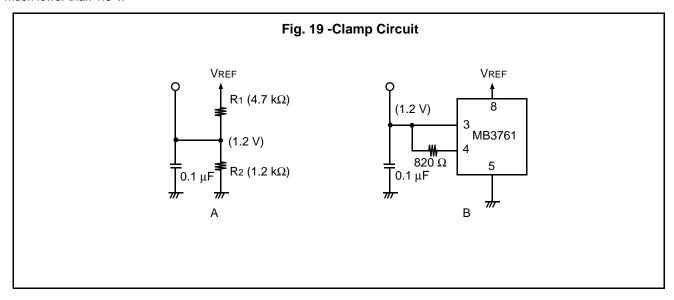
When VTH = 2.5 V, CT can be provided by followings.

tcycle - tP =
$$\frac{1}{\text{fosc}} \times \frac{(3.5 - \text{VL}) + (3.5 - \text{VTH})}{\text{fosc}(3.5 - 1.5) \times 2}$$



$$\begin{split} &\text{fOSC} \simeq \ \, \frac{1}{0.8 \, \text{x CT x RT}} \\ &\text{CT} \simeq \ \, \frac{1}{0.8 \, \text{x RT}} \ \, \text{x} \quad \frac{4}{4.5 \, \text{- VL}} \quad \text{(tcycle - tP) [pF] (RT: kΩ, tcycle, tP: ns)} \end{split}$$

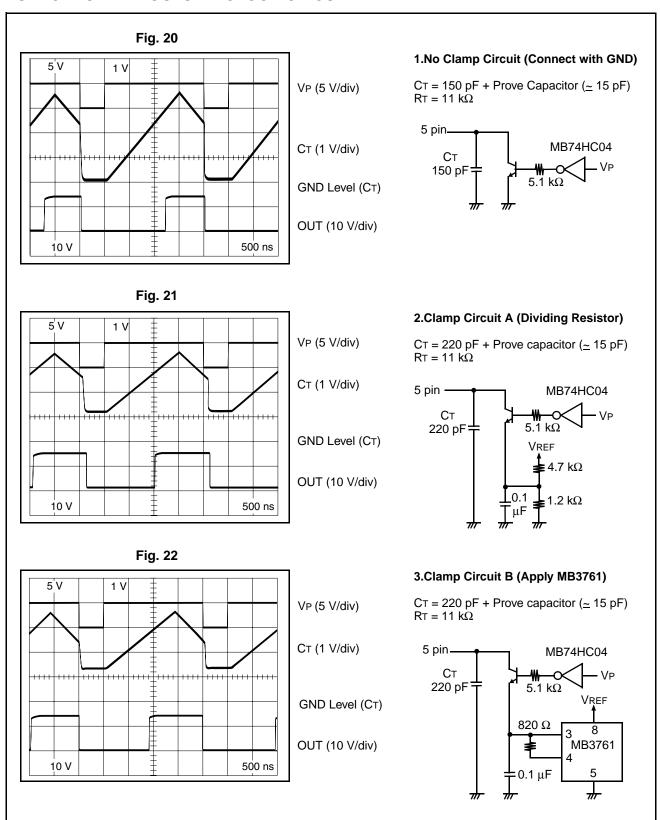
Make VL high for a large duty cycle for the clamp circuit. The circuits below can be used because the clamp voltage must be much lower than 1.5 V.

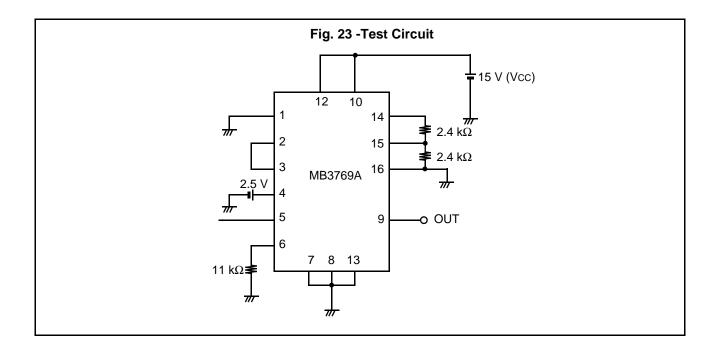


In circuit A, R1 and R2 must be determined considering the effects of tP, R, or RT.

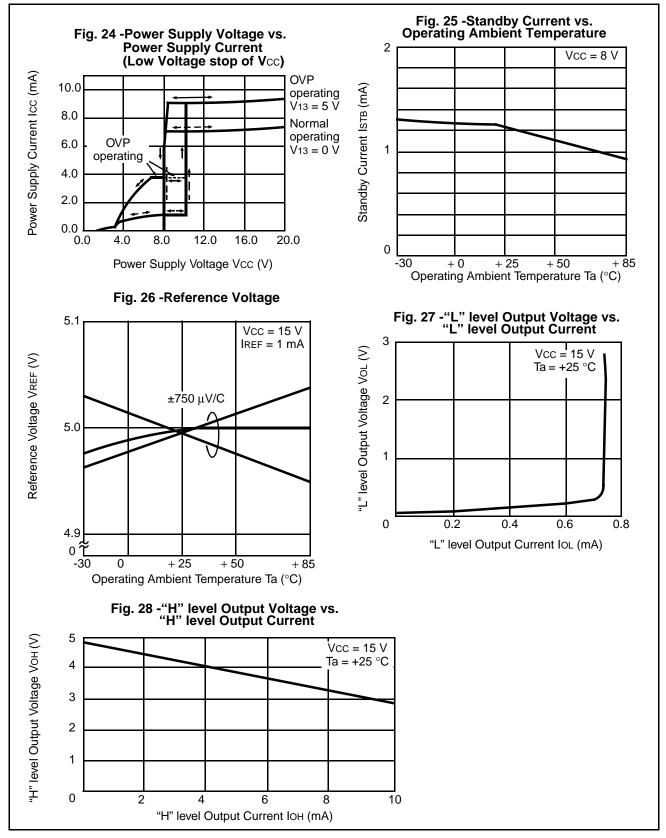
The transistor saturation voltage must be very small (<0.15 V) for any clamp circuit, so a transistor with a very small VCE (sat) should be used.

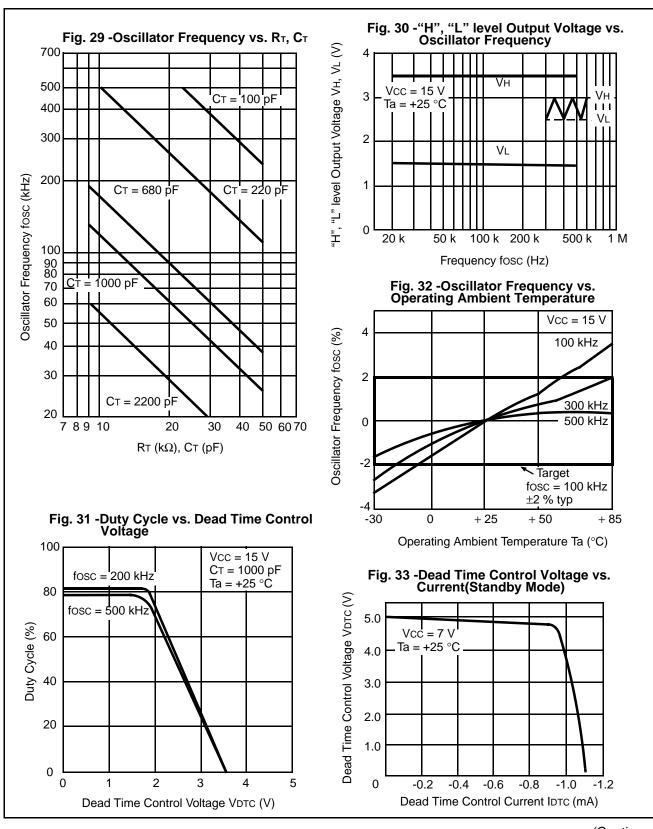
■ SYNCHRONIZED OUTSIDE CLOCK CIRCUIT

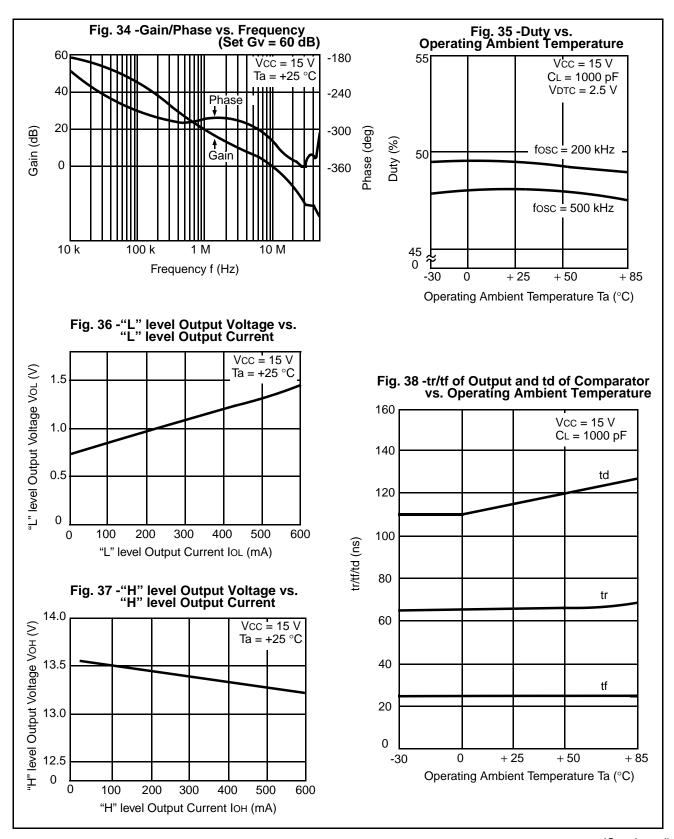


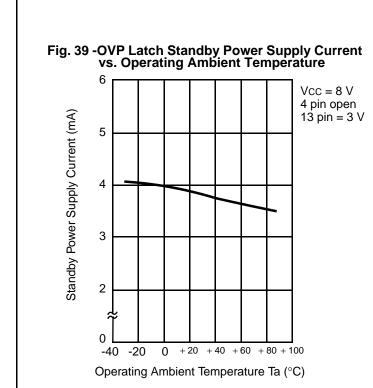


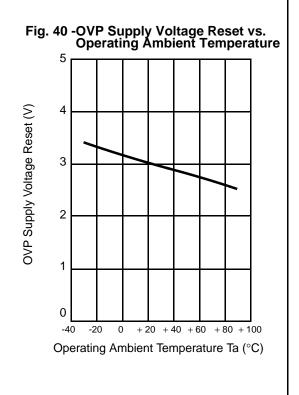
■ TYPICAL PERFORMANCE CHARACTERISTICS











■ NOTES ON USE

- Take account of common impedance when designing the earth line on a printed wiring board.
- Take measures against static electricity.
 - For semiconductors, use antistatic or conductive containers.
 - When storing or carrying a printed circuit board after chip mounting, put it in a conductive bag or container.
 - The work table, tools and measuring instruments must be grounded.
 - The worker must put on a grounding device containing 250 k Ω to 1 M Ω resistors in series.
- · Do not apply a negative voltage
 - Applying a negative voltage of -0.3 V or less to an LSI may generate a parasitic transistor, resulting in malfunction.

■ ORDERING INFORMATION

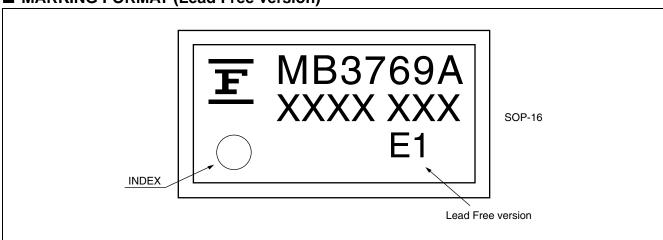
Part number	Package	Remarks
MB3769APF-□□□	16-pin plastic SOP (FPT-16P-M06)	Conventional version
MB3769APF-□□□E1	16-pin plastic SOP (FPT-16P-M06)	Lead Free version

■ RoHS Compliance Information of Lead (Pb) Free version

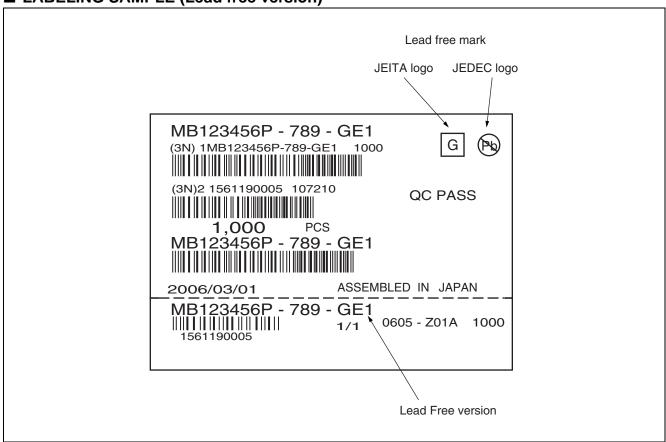
The LSI products of Fujitsu with "E1" are compliant with RoHS Directive, and has observed the standard of lead, cadmium, mercury, Hexavalent chromium, polybrominated biphenyls (PBB), and polybrominated diphenyl ethers (PBDE).

The product that conforms to this standard is added "E1" at the end of the part number.

■ MARKING FORMAT (Lead Free version)



■ LABELING SAMPLE (Lead free version)

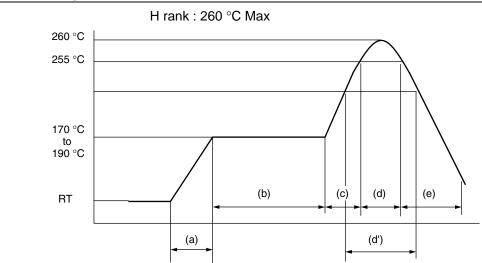


■ MB3769APF-□□□E1 RECOMMENDED CONDITIONS OF MOISTURE SENSITIVITY LEVEL

Item	Condition				
Mounting Method	IR (infrared reflow), Manual soldering (partial heating method)				
Mounting times	2 times				
	Before opening	Please use it within two years after Manufacture.			
Storage period	From opening to the 2nd reflow	Less than 8 days			
	When the storage period after opening was exceeded	Please processes within 8 days after baking (125 °C, 24H)			
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)				

[Temperature Profile for FJ Standard IR Reflow]

(1) IR (infrared reflow)



(a) Temperature Increase gradient : Average 1 °C/s to 4 °C/s

(b) Preliminary heating : Temperature 170 °C to 190 °C, 60s to 180s

(c) Temperature Increase gradient : Average 1 °C/s to 4 °C/s

(d) Actual heating : Temperature 260 $^{\circ}$ C Max; 255 $^{\circ}$ C or more, 10s or less

(d') : Temperature 230 °C or more, 40s or less

or

Temperature 225 °C or more, 60s or less

or

Temperature 220 $^{\circ}\text{C}$ or more, 80s or less

(e) Cooling : Natural cooling or forced cooling

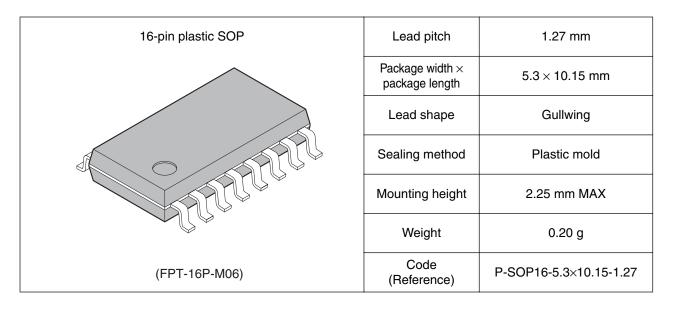
Note: Temperature: the top of the package body

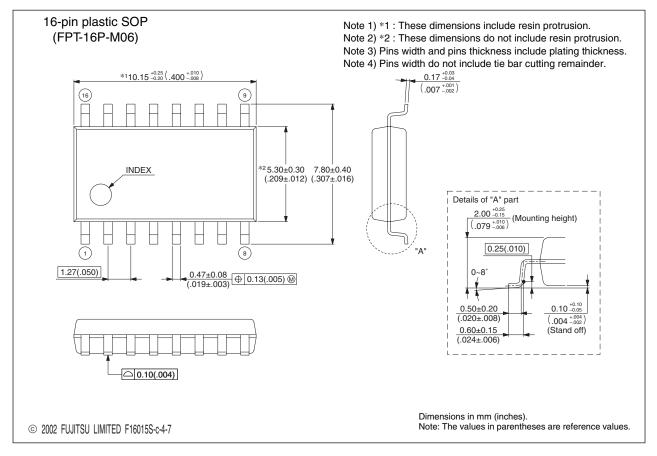
(2) Manual soldering (partial heating method)

Conditions : Temperature 400 $^{\circ}$ C Max

Times : 5 s max/pin

■ PACKAGE DIMENSION





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